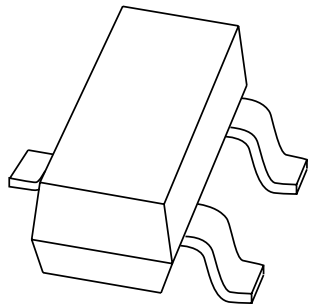


DATA SHEET



PBR941B UHF wideband transistor

Preliminary specification

2001 Jan 18

UHF wideband transistor

PBR941B

FEATURES

- Small size
- Low noise
- Low distortion
- High gain
- Gold metallization ensures excellent reliability.

APPLICATIONS

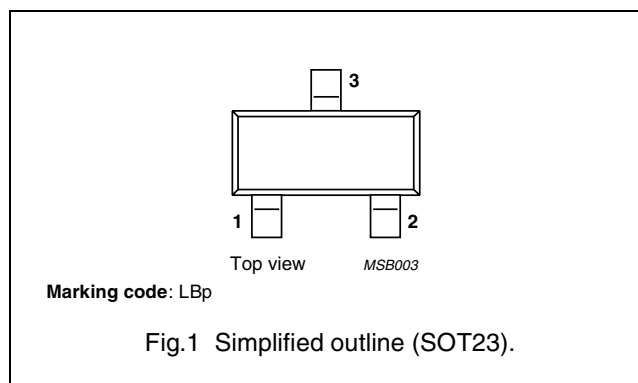
- Communication and instrumentation systems.

DESCRIPTION

Silicon NPN transistor in a surface mount 3-pin SOT23 package. The transistor is primarily intended for wideband applications in the GHz range in the RF front end of analog and digital cellular telephones, cordless phones, radar detectors, pagers and satellite TV-tuners.

PINNING SOT23

PIN	DESCRIPTION
1	base
2	emitter
3	collector



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
C_{re}	feedback capacitance	$I_C = 0$; $V_{CB} = 6$ V; $f = 1$ MHz	–	0.3	–	pF
f_T	transition frequency	$I_C = 15$ mA; $V_{CE} = 6$ V; $f_m = 1$ GHz	7	9	–	GHz
G_{UM}	maximum unilateral power gain	$I_C = 15$ mA; $V_{CE} = 6$ V; $T_{amb} = 25$ °C; $f = 1$ GHz	–	16	–	dB
NF	noise figure	$\Gamma_S = \Gamma_{opt}$; $I_C = 5$ mA; $V_{CE} = 6$ V; $f = 1$ GHz	–	1.5	2.5	dB
P_{tot}	total power dissipation	$T_s = 60$ °C; note 1	–	–	360	mW
$R_{th\ j-s}$	thermal resistance from junction to soldering point		–	–	320	K/W

Note

1. T_s is the temperature at the soldering point of the collector pin.

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	10	V
V_{EBO}	emitter-base voltage	open collector	–	1.5	V
I_C	collector current (DC)		–	50	mA
$I_{C(AV)}$	average collector current		–	50	mA
P_{tot}	total power dissipation	$T_s = 60\text{ °C}$; note 1	–	360	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

Note

- T_s is the temperature at the soldering point of the collector pin.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-s}$	thermal resistance from junction to soldering point	320	K/W

UHF wideband transistor

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CHARACTERISTICST_j = 25 °C unless otherwise specified.

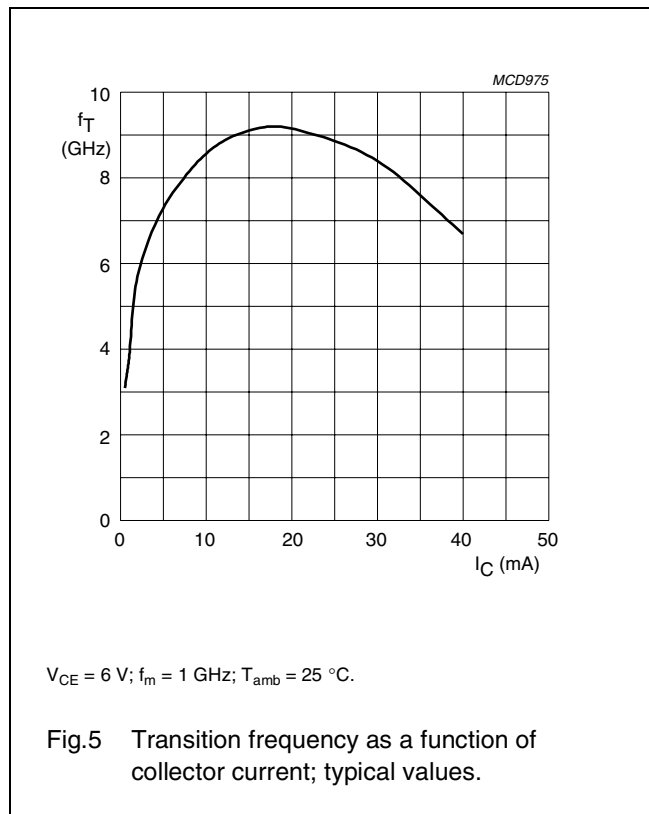
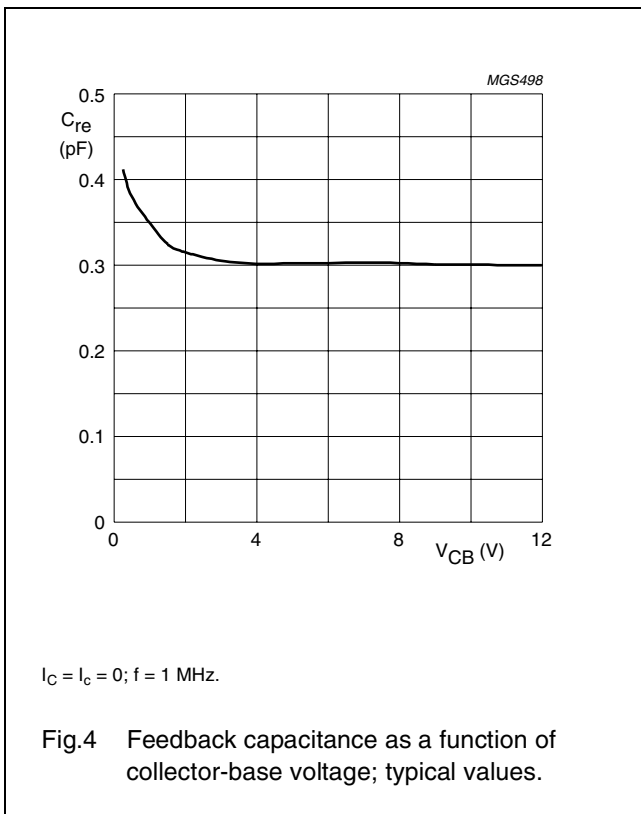
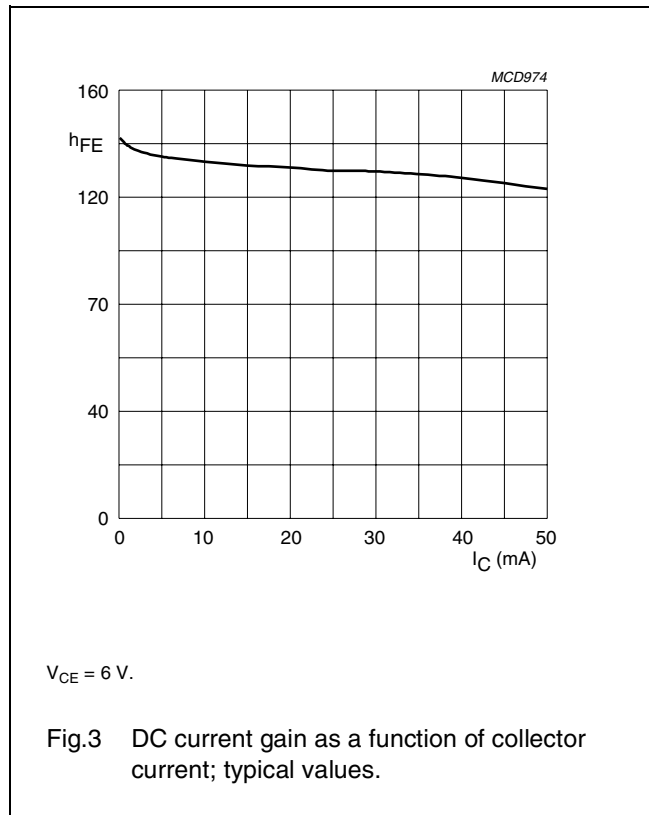
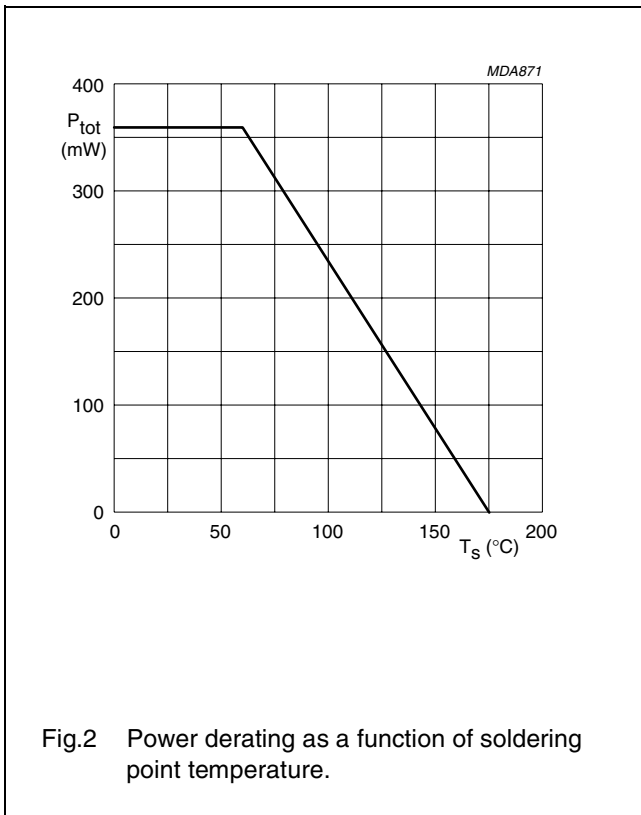
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
DC characteristics						
V _{(BR)CBO}	collector-base breakdown voltage	I _C = 100 μA; I _E = 0	20	–	–	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I _C = 100 μA; I _B = 0	10	–	–	V
V _{(BR)EBO}	emitter-base breakdown voltage	I _E = 10 μA; I _C = 0	1.5	–	–	V
V _{BEF}	forward base-emitter voltage	I _E = 25 mA	–	–	1.05	V
I _{CBO}	collector-base leakage current	V _{CB} = 10 V; I _E = 0	–	–	100	nA
I _{EBO}	emitter-base leakage current	V _{EB} = 1 V; I _C = 0	–	–	100	nA
h _{FE}	DC current gain	I _C = 5 mA; V _{CE} = 6 V	100	150	200	
		I _C = 15 mA; V _{CE} = 6 V	–	150	–	
AC characteristics						
C _{re}	feedback capacitance	I _C = 0; V _{CB} = 6 V; f = 1 MHz	–	0.3	–	pF
f _T	transition frequency	I _C = 15 mA; V _{CE} = 6 V; f _m = 1 GHz	7	9	–	GHz
S ₂₁ ²	insertion gain	I _C = 15 mA; V _{CE} = 6 V; f = 1 GHz	13	15	–	dB
G _{UM}	maximum unilateral power gain; note 1	I _C = 15 mA; V _{CE} = 6 V; T _{amb} = 25 °C; f = 1 GHz	–	16	–	dB
		I _C = 15 mA; V _{CE} = 6 V; T _{amb} = 25 °C; f = 2 GHz	–	10	–	dB
NF	noise figure	Γ _S = Γ _{opt} ; I _C = 5 mA; V _{CE} = 6 V; f = 1 GHz	–	1.5	2.5	dB
		Γ _S = Γ _{opt} ; I _C = 5 mA; V _{CE} = 6 V; f = 2 GHz	–	2.1	–	dB

Note

1. G_{UM} is the maximum unilateral power gain, assuming s₁₂ is zero.
$$G_{UM} = 10 \log \frac{|s_{21}|^2}{(1 - |s_{11}|^2)(1 - |s_{22}|^2)} \text{ dB}$$

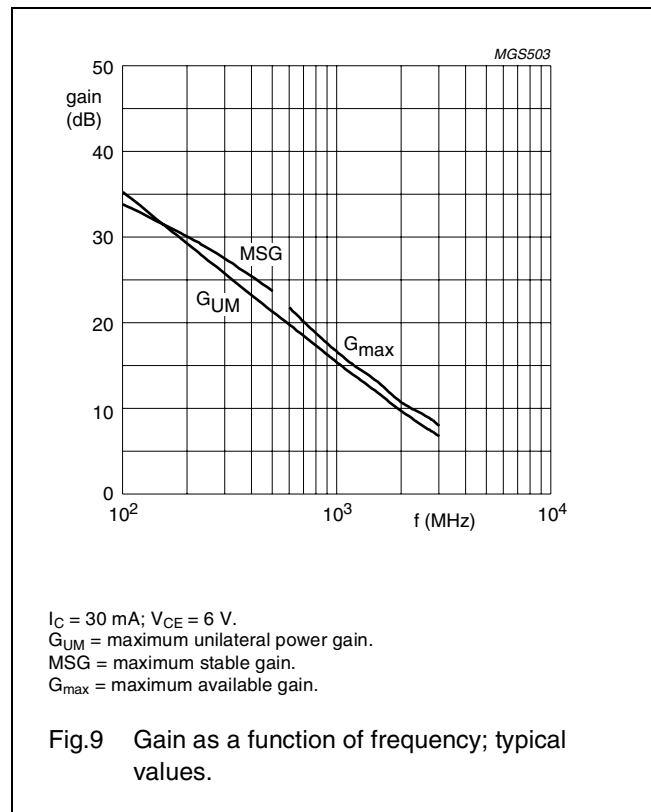
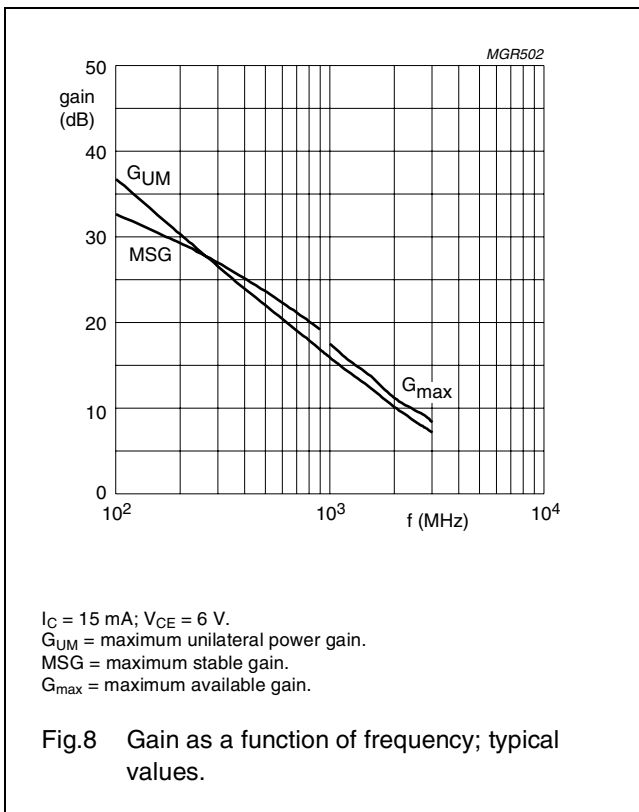
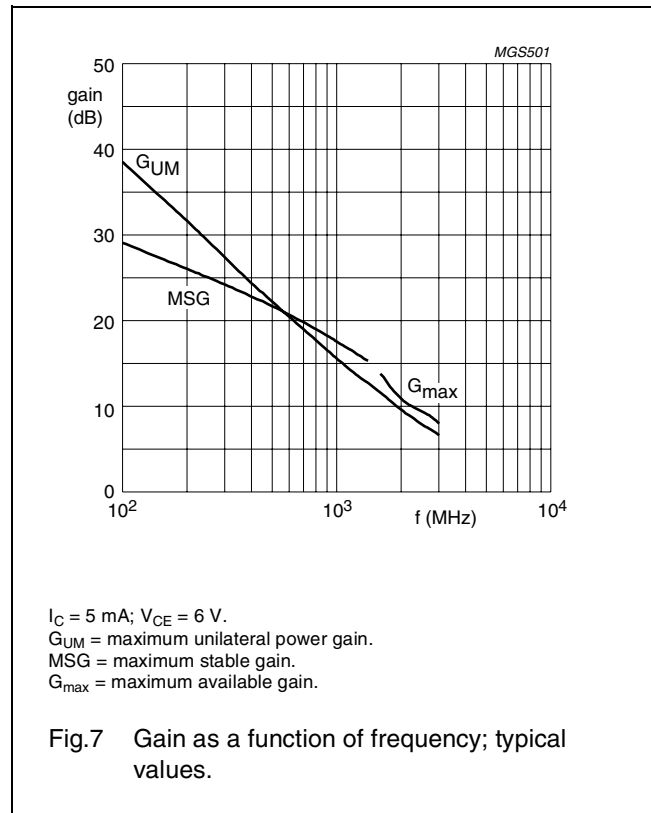
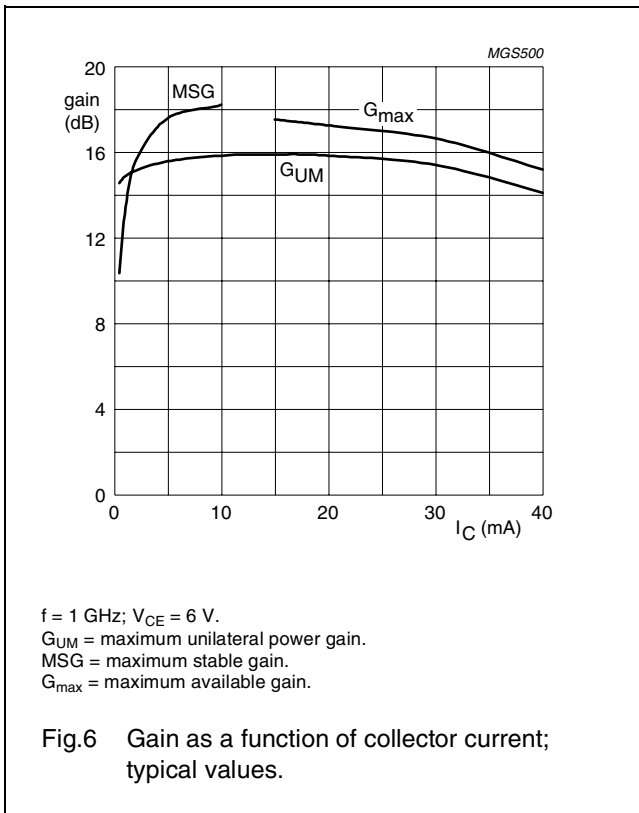
UHF wideband transistor

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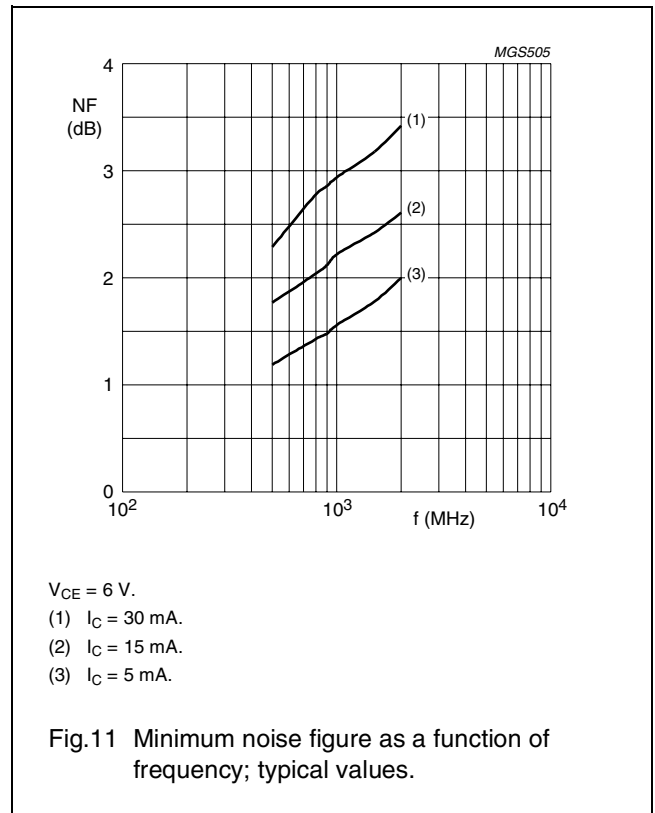
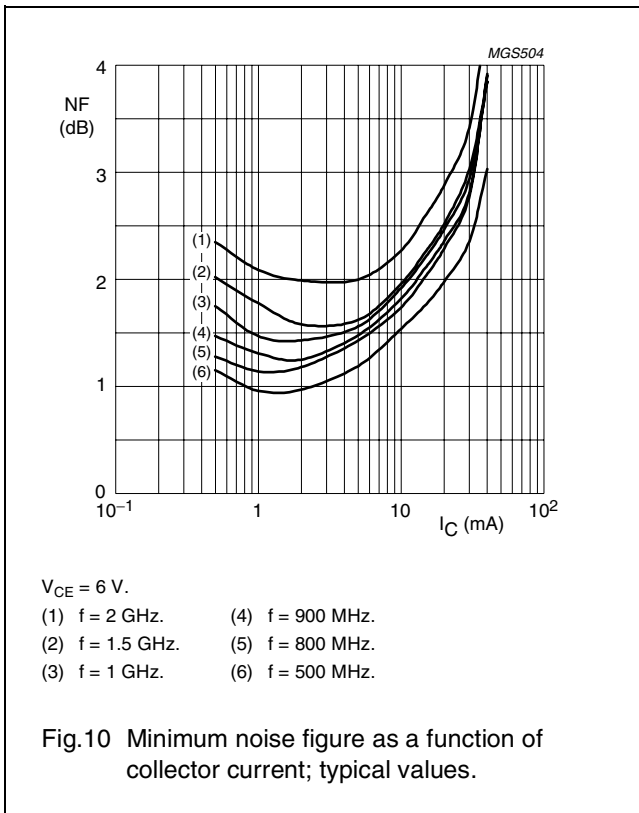
UHF wideband transistor

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UHF wideband transistor

PBR941B



UHF wideband transistor

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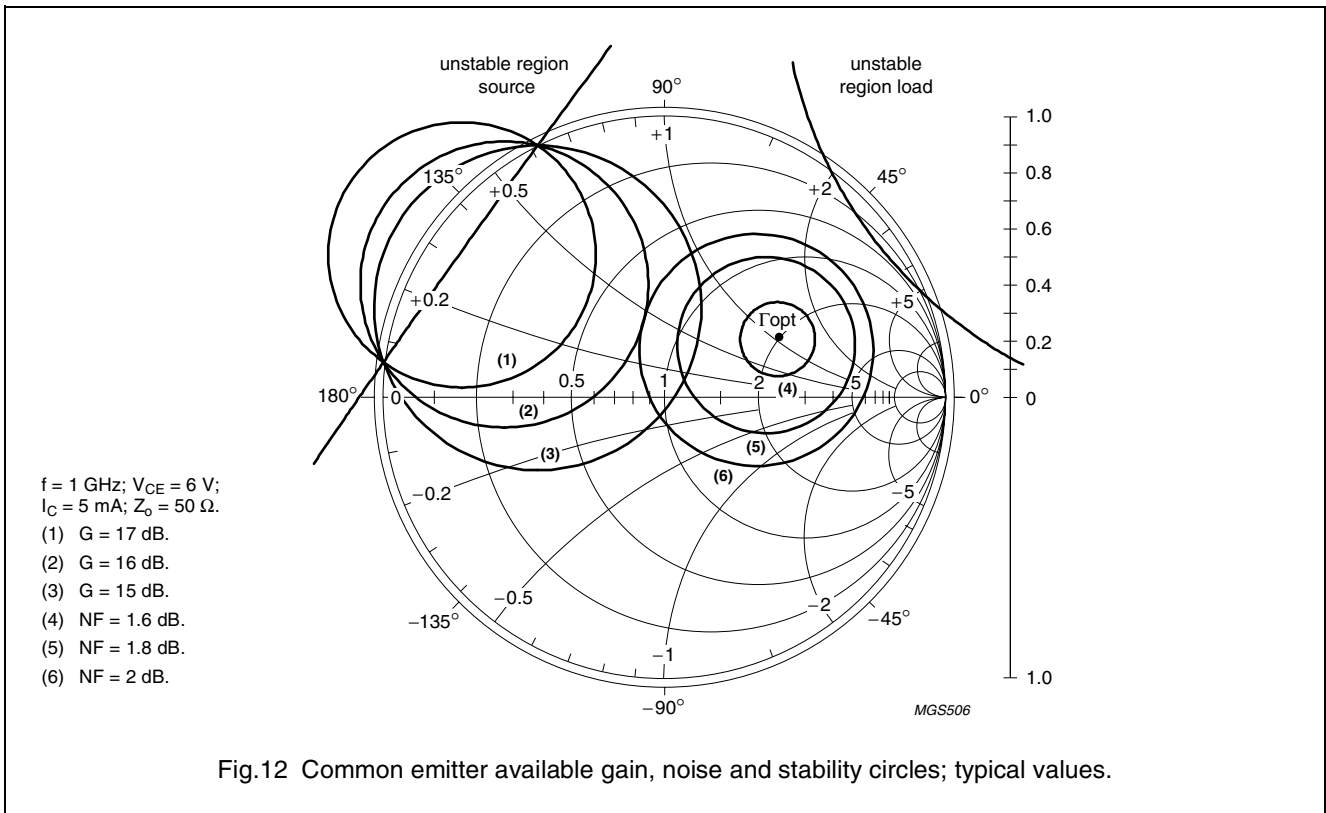


Fig.12 Common emitter available gain, noise and stability circles; typical values.

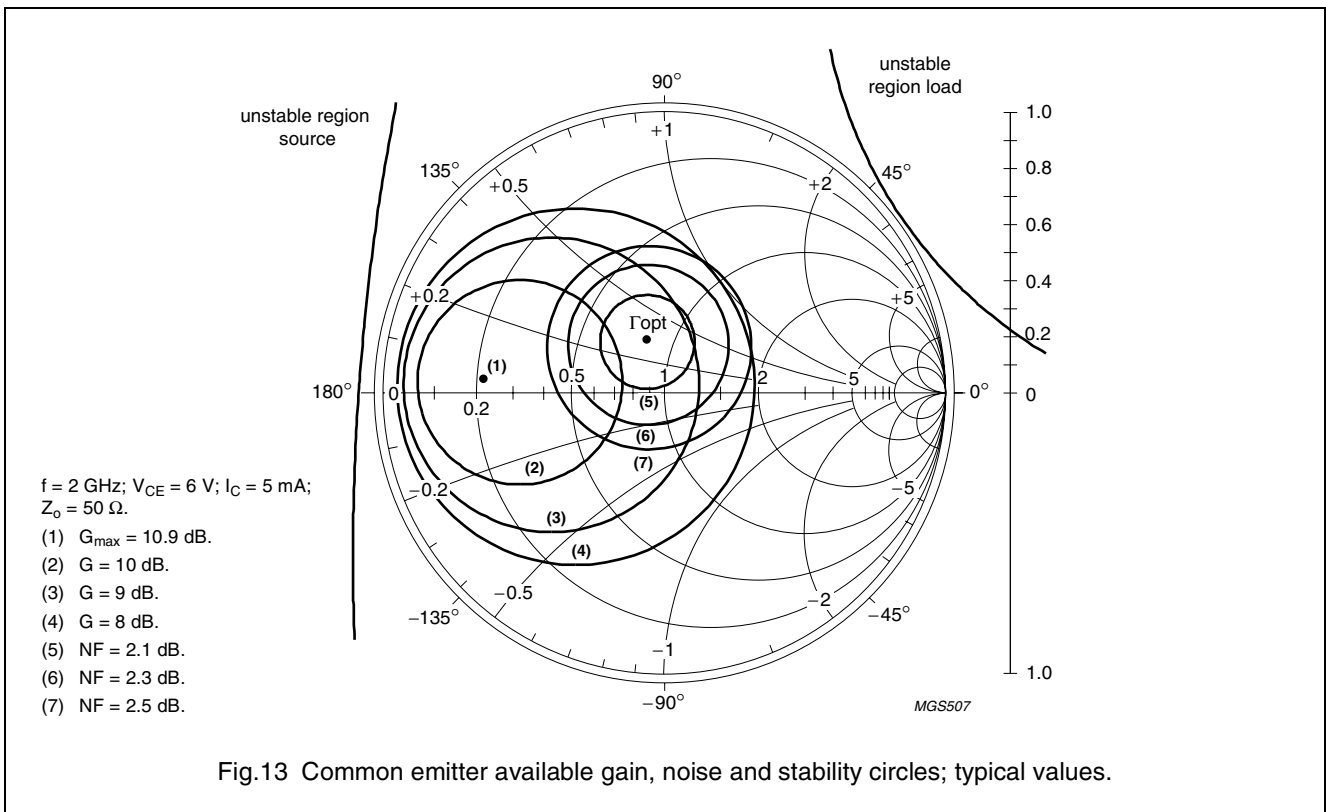
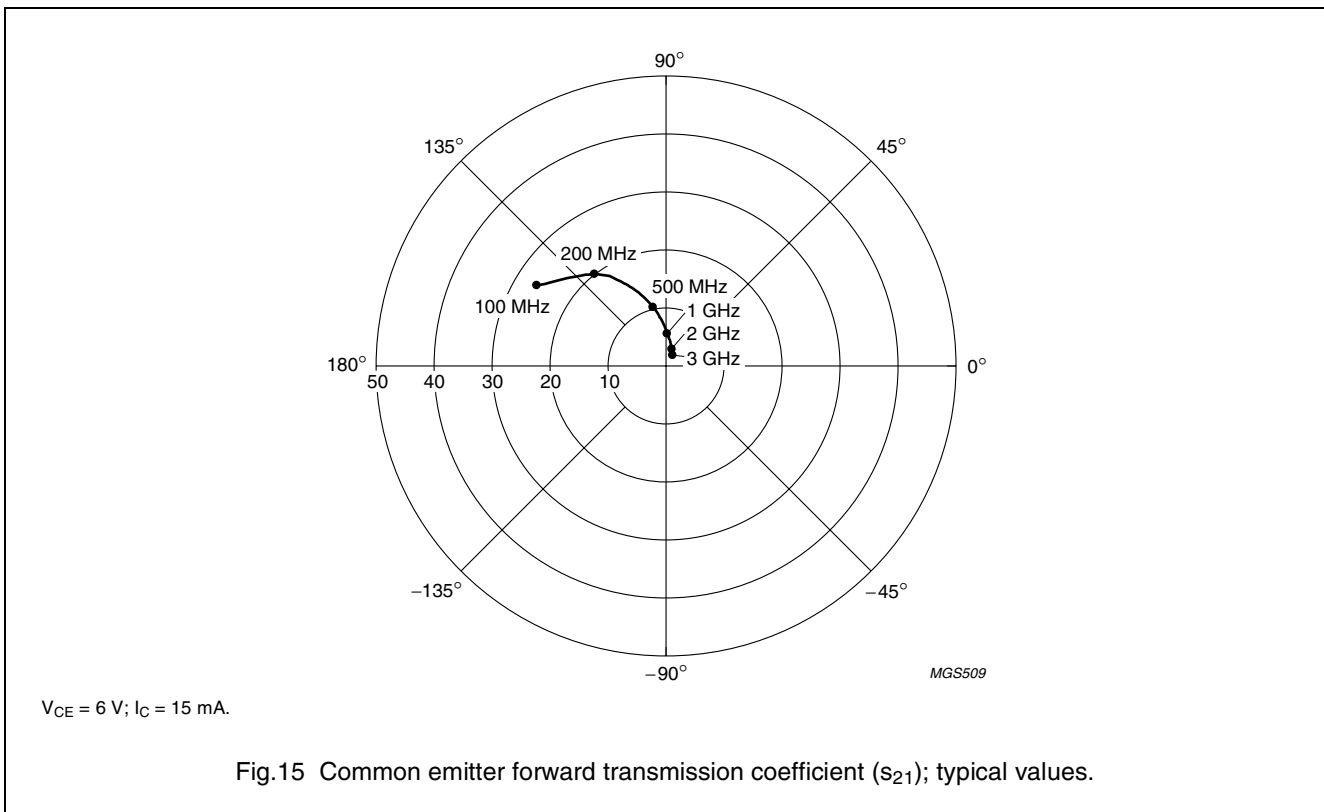
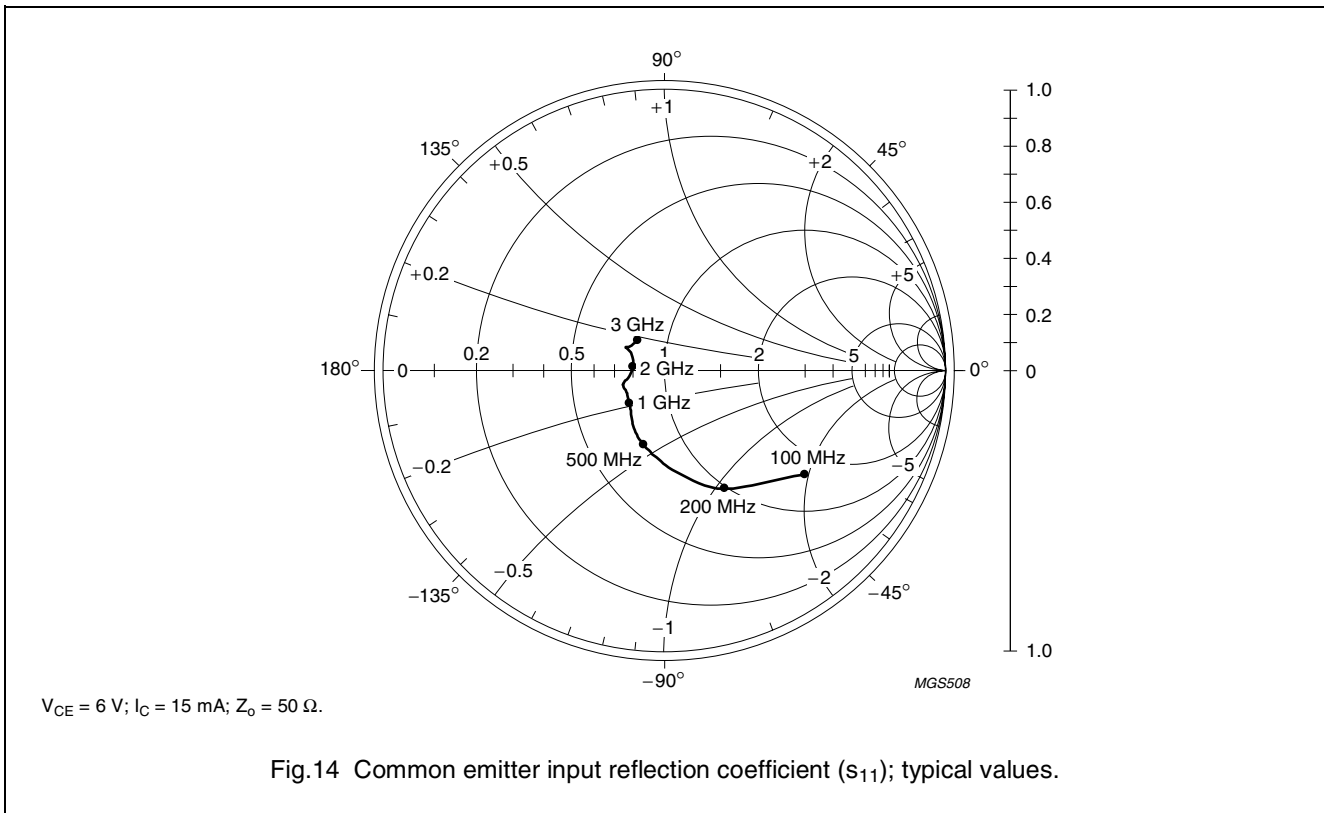


Fig.13 Common emitter available gain, noise and stability circles; typical values.

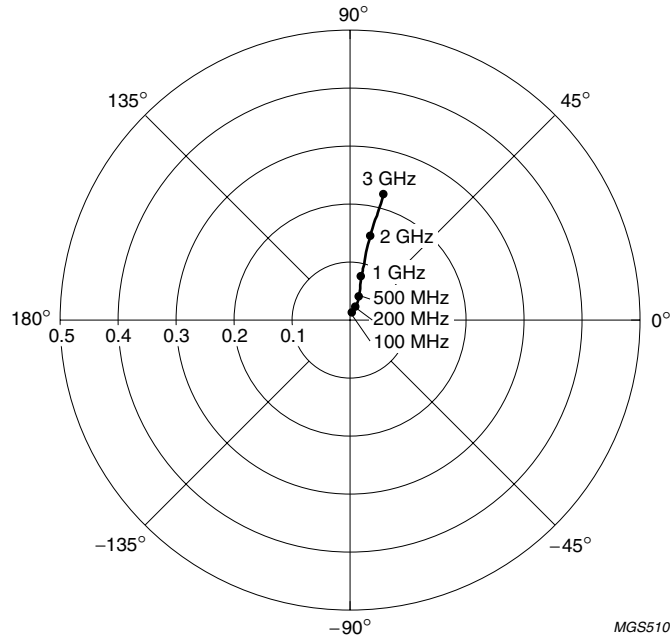
UHF wideband transistor

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UHF wideband transistor

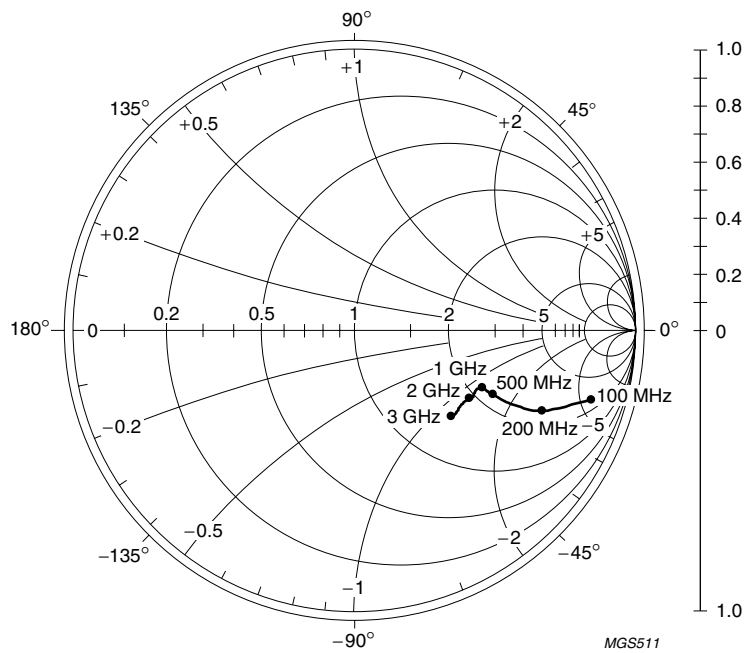
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$V_{CE} = 6\text{ V}; I_C = 15\text{ mA}$.

MGS510

Fig.16 Common emitter reverse transmission coefficient (s_{12}); typical values.



$V_{CE} = 6\text{ V}; I_C = 15\text{ mA}; Z_0 = 50\ \Omega$.

MGS511

Fig.17 Common emitter output reflection coefficient (s_{22}); typical values.

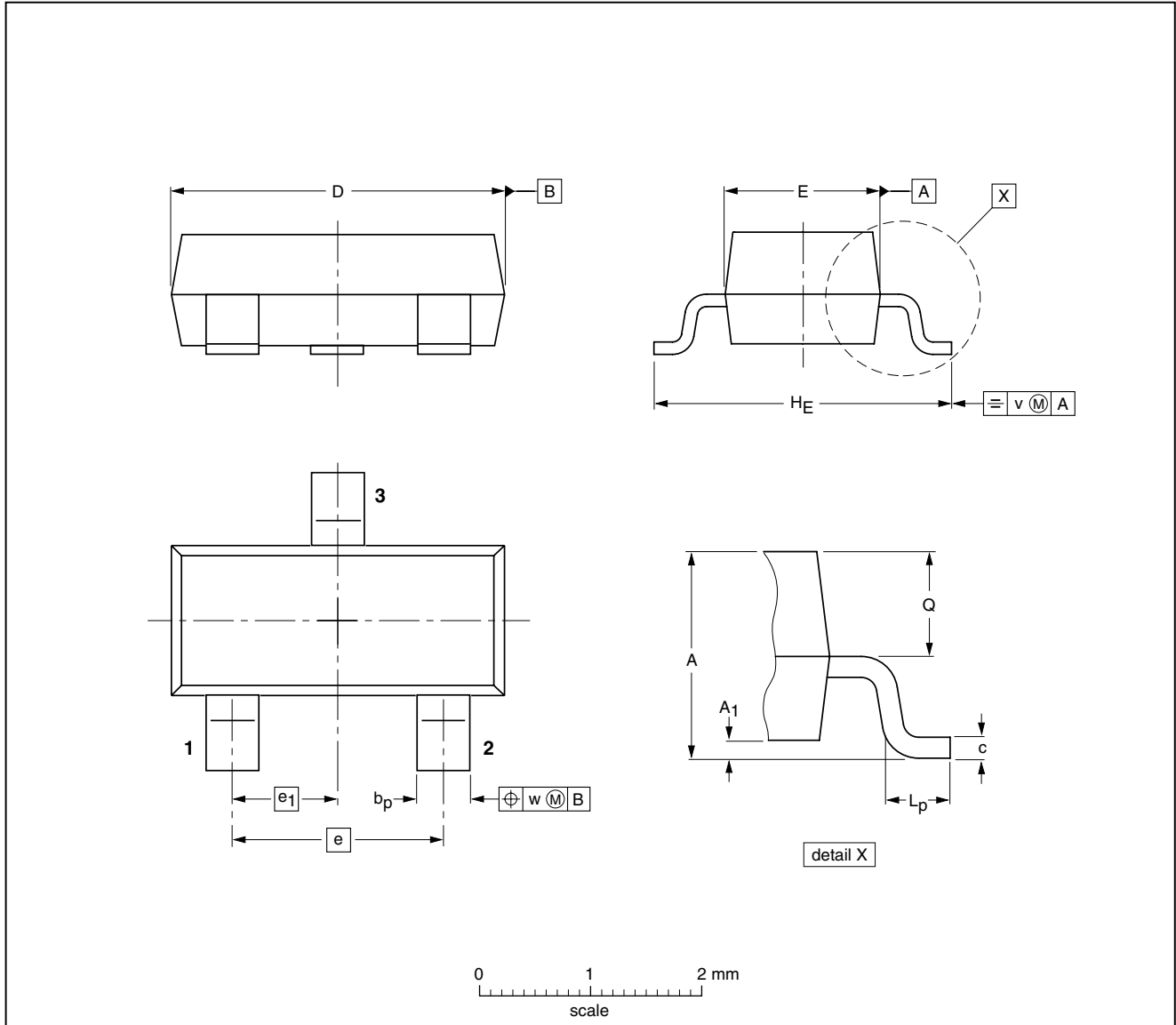
UHF wideband transistor

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				97-02-28 99-09-13

UHF wideband transistor

PBR941B

DATA SHEET STATUS

DATA SHEET STATUS	PRODUCT STATUS	DEFINITIONS ⁽¹⁾
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.

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